GENERAL DESCRIPTION

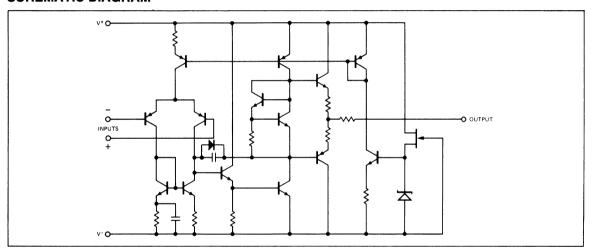
The 4558 integrated circuit is a high gain operational amplifier internally compensated and constructed on a single silicon chip using the planar epitaxial process.

Combining all of the outstanding features of the 741 with the close parameter matching and tracking of a dual device on a monolithic chip results in unique performance characteristics. Excellent channel separation allows the use of the dual device in all single 741 operational amplifier applications providing the highest possible packaging density. It is especially well suited for applications in differential-in, differential-out as well as in potentiometric amplifiers and where gain and phase matched channels are mandatory.

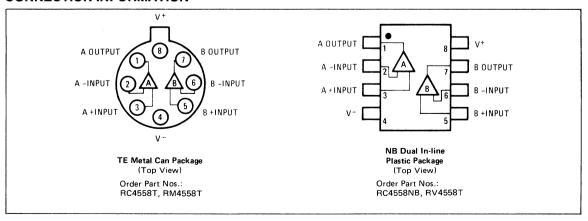
DESIGN FEATURES

- Supply Voltage ±18 V
- Continuous Short-Circuit Protection
- No Frequency Compensation Required
- No Latch-Up
- Unity Gain Bandwidth 3 MHz
- Large Common-Mode and Differential Voltage Ranges
- Low Power Consumption
- Parameter Tracking Over Temperature Range
- Gain and Phase Match Between Amplifiers

SCHEMATIC DIAGRAM



CONNECTION INFORMATION





ABSOLUTE MAXIMUM RATINGS

Supply Voltage RM4558: ±22V	Operating Temperature Range RM4558: -55°C to +125°C
RC4558: ±18V	RV4558: -40°C to +85°C
Internal Power Dissipation (Note 1) 500mW	RC4558: 0°C to +70°C
Differential Input Voltage ±30V	Lead Temperature (Soldering, 60s)
Input Voltage (Note 2) ±15V	Output Short-Circuit Duration (Note 3) Indefinite
Storage Temperature Range65°C to +150°C	

ELECTRICAL CHARACTERISTICS (V_{CC} = ±15V, T_A = 25°C unless otherwise specified)

PARAMETER	CONDITIONS	RM4558			RV/RC4558			
		MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Input Offset Voltage	Rs≤10kΩ		1.0	5.0		2.0	6.0	mV
Input Offset Current			30	200		30	200	nΑ
Input Bias Current			200	500		200	500	nΑ
Input Resistance		0.3	1.0		0.3	1.0		Ω M
Large-Signal Voltage Gain	$R_L \ge 2k\Omega$ $V_{out} = \pm 10V$	50,000	200,000		20,000	100,000		
Output Voltage Swing	R _L ≥ 10kΩ	±12	±14		±12	±14		V
	$R_L \ge 2k\Omega$	±10	±13		±10	±13		V
Input Voltage Range		±12	±13		±12	±13		V
Common Mode Rejection Ratio	Rs≤10kΩ	70	90		70	90		dB
Supply Voltage Rejection Ratio	R _S ≤10kΩ		30	150		30	150	μV/V
Power Consumption			100	170		100	170	mW
Transient Response (unity gain) Risetime	$V_{IN} = 20mV$ $R_L = 2k\Omega$ $C_L \le 100pF$		0.3			0.3		μs
Overshoot			5.0			5.0		%
Slew Rate (unity gain)	R _L ≥2kΩ		0.5			0.5		V/μs
Channel Separation (open loop)	f = 10kHz Rs = 1kΩ	,	70			70		dB
(Gain = 100)	f = 10kHz Rs = $1k\Omega$		83			83		dB
The following specifications apply f $-40^{\circ}\text{C} \le T_{\text{A}} \le +85^{\circ}\text{C}$ for RV4558		+125ºĊ for	RM4558; 0)°C ≤ T⊿	√< +70°C	for RC455	8;	
Input Offset Voltage	$R_S \leq 10k\Omega$			6.0			7.5	mV
Input Offset Current				500			300/500*	nΑ
Input Bias Current				1.5			.8/1.5*	nΑ
Large-Signal Voltage Gain	$R_L \ge 2k\Omega$ $V_{out} = \pm 10V$	25,000			15,000			
Output Voltage Swing	R _L ≥2kΩ	±10			±10			V
Power Consumption	V _S = ±15V T _A = +125°C T _A = -55°C		90 120	150 200		90 120	150 200	mW

MATCHING CHARACTERISTICS

(V_{CC} = ± 15 V, T_A = 25°C unless otherwise specified)

*RV4558

PARAMETER	CONDITIONS	RM4558 TYP	RC4558 TYP	UNITS
Voltage Gain	$R_1 \geqslant 2k\Omega$	±.5	±1.0	dB
Input Bias Current	_	±15	±15	nA
Input Offset Current		±7.5	±7.5	l nA
Input Offset Voltage	R _S ≥ 10kΩ	±.1	±.2	mV

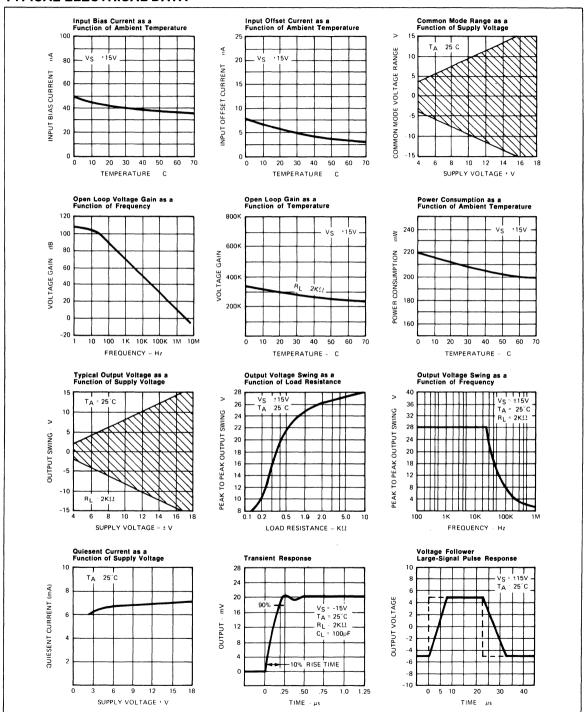
NOTE 1: Rating applies for case temperatures to 125°C; derate linearly at 6.5mW/°C for ambient temperatures above +75°C for RM4558.

NOTE 2: For supply voltages less than ±15V, the absolute maximum input voltage is equal to the supply voltage.

NOTE 3: Short circuit may be to ground or either supply. Rating applies to +125°C case temperature or +75°C ambient temperature for RC4558 and to +85°C ambient temperature for RV4558.



TYPICAL ELECTRICAL DATA





TYPICAL ELECTRICAL DATA

